



Docket No.: 061352-0041

101
COFC
VT
PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Customer Number: 20277

Hiroyuki FURUYA, et al.

Confirmation Number: 2093

Application No.: 10/620,432

Group Art Unit: 2812

Filed: July 17, 2003

Examiner: MULPURI, SAVITRI

For: METHOD OF FABRICATING NITRIDE BASED SEMICONDUCTOR
SUBSTRATE AND METHOD OF FABRICATING NITRIDE BASED
SEMICONDUCTOR DEVICE

RESPONSE TO COMMUNICATION DATED JUNE 21, 2005

Attn: Decisions and Certificate of Correction Branch

**Certificate
AUG 08 2005
of Correction**

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In response to your communication dated June 21, 2005, denying the request for correction of the error under Foreign Patent Documents, we respectfully request reconsideration of the Certificate of Correction regarding insertion of – KR 2010583 A-- on the title page of Letters Patent US 6,806,109 under "FOREIGN PATENT DOCUMENTS" for the following reason (Photocopy of the Certificate of Correction request filed on May 26, 2005 is attached). Contrary to the conclusion reached in denying the previous request for the Certificate of Correction, the reference in question has been previously considered during prosecution as is made clear by the Examiner's initials placed next the reference on the PTO-1449 form signed by the Examiner and returned to the Applicants. A photocopy of this

PTO-1449 form initialed by the examiner and returned to us on May 6, 2004 as part of the Notice of Allowance is attached. As is clear, the PTO-1449 form shows the initials of the examiner reflecting that the reference KR 2010583 was considered.

In light of this evidence we ask that a Certificate of Correction be issued reflecting the Korean Reference -KR 2010583 A --.

Respectfully submitted,

McDERMOTT WILL & EMERY LLP

Michael E. Fogarty
Registration No. 36,139

Please recognize our Customer No. 20277
as our correspondence address.

600 13th Street, N.W.
Washington, DC 20005-3096
Phone: 202.756.8000 MEF:jgh
Facsimile: 202.756.8087
Date: August 3, 2005

AUG 09 2005



UNITED STATES PATENT AND TRADEMARK OFFICE

Commissioner for Patents
United States Patent and Trademark Office
P.O. Box 1450
Alexandria, VA 22313-1450
www.uspto.gov

Date : June 21, 2005

Michael E. Fogarty
McDERMOTT WILLIAMS & EMERY
600 13TH Street, NW
Washington, DC 20005-3096

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Patent No: 6806109 B2

Applicant: Hiroyuki Furuya, et al.

Issued: October 19, 2004

Title: **METHOD OF FABRICATING NITRIDE BASED SEMICONDUCTOR SUBSTRATE AND METHOD OF FABRICATING NITRIDE BASED SEMICONDUCTOR DEVICE**

Request for Certificate of Correction:

Consideration had been given to your request for the issuance of a certificate of correction for the above-identified patent under the provisions of Rule 1.322.

Respecting the alleged error under Foreign Patent Documents, the patent is printer in accordance with the record, since the references was not in conformance and not considered. Therefore, no correction is in order here under 1.322 or 1.323.

In view of the foregoing, your request in this matter is hereby **denied**.

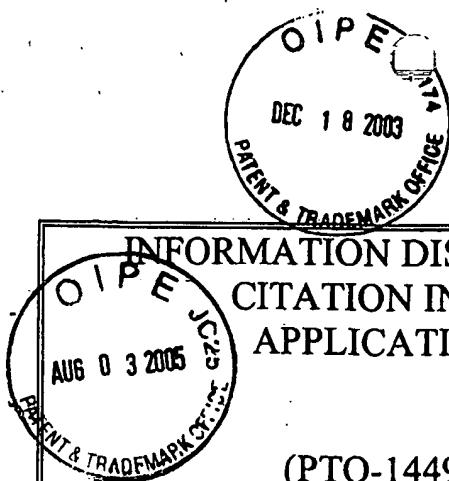
A certificate of correction will be issued to correct the remaining error mentioned in your request.

Correspondence concerning this matter should be filed and directed to Decisions and Certificate of Correction Branch.

Virginia Tolbert
For Cecelia Newman, Supervisor
Decisions and Certificate of Correction
(703) 305-8309 or 308-9390 ext. 113

vt

AUG 09 2005



SHEET 1 OF 1

INFORMATION DISCLOSURE
CITATION IN AN
APPLICATION

(PTO-1449)

ATTY. DOCKET NO.
61352-041

SERIAL NO.
10/620,432

APPLICANT
Hiroyuki FURUYA, et al.

FILING DATE
July 17, 2003

GROUP
2812

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes -Number & Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
Gu		JP 2001-176813 A (w/ English Abstract)	06/29/2001	NICHIA CHEM. IND., LTD.			
		JP 2001-342100 A (w/ partial English translation)	12/11/2001	TOSHIBA CORP.			
		EP 1 278 233 A1 (WO 01/084608)	01/22/2003	TOYODA GOSEI CO., LTD.			
		JP 2001-168042 A (w/ English Abstract)(WO 00/55893)	06/22/2001	MITSUBISHI CABLE IND., LTD.			
		EP 1 184 897 A1	03/06/2000	MITSUBISHI CABLE IND., LTD.			
		JP 2001-93837 A (w/ English Abstract)	04/06/2001	CANON INC.			
		J 2002-353152 A (w/ English Abstract)	12/06/2002	MATSUSHITA ELECTRIC IND. CO., LTD.			
		JP 2002-110569 A (w/ English Abstract)	04/12/2002	MATSUSHITA ELECTRIC IND. CO., LTD.			
		JP 2000-228539 A (w/ English Abstract)	08/15/2000	SHARP CORP.			
		JP 11-191657 (w/ English Abstract)	07/13/1999	NICHIA CHEM. IND., LTD.			
		JP 2001-313259 A		Copy not enclosed.			
		AU 3607601 A		Copy not enclosed.			
		JP 2000-156002 A		Copy not enclosed.			
		JP 2000-331947 A		Copy not enclosed.			
		JP 2000-331937 A		Copy not enclosed.			
Gu		KR 2010583 A		Copy not enclosed.			

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
Gu		I. KIDOGUCHI et al., "Improvement of Crystalline Quality in GaN Films by Air-Bridged Lateral Epitaxial Growth", Jpn. J. Appl. Phys., Part 2, Vol. 39, No. 5B, (2000), pages L453-456.	
		S. NAKAMURA, "InGaN/GaN/A1GaN-based laser diodes grown on epitaxially laterally overgrown GaN", Journal of Materials Research, Commentaries and Reviews, Vol. 14, No. 7, July 1999, pages 2716-2731.	
Gu		S. NAKAMURA et al., "High-Power, Long-Lifetime InGaN/GaN/A1GaN-Based Laser Diodes Grown on Pure GaN Substrates", Jpn. J. Appl. Phys., Vol. 37, 15 March 1998, pages L309-L312.	

EXAMINER

DATE CONSIDERED

3/9/04

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered.
Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

Applicant: Hiroyuki FURUYA, et al. Docket No. 061352-0041 Serial No. 10/620,4
 Title: METHOD OF FABRICATING NITRIDE BASED SEMICONDUCTOR SUBSTRATE AND METHOD OF FABRICATING NITRIDE BASED SEMICONDUCTOR DEVICE

Date Sent: 5/26/2005 Hand Carried Fax Electronic Cert. of Mailing First Class Mail Express Mail No. 6,806,10

Transmittal Letter

New Patent App Utility Design Cont. CIP

Div. PCT RCE Prov

Other: _____

Letter submitting _____ pages of drawings

pages of Specification

Req. for Approval of Drawing Amendments

pages of Claims

Req. for Oral Hearing

pages of Abstract

Not. of Appeal Appeal Brief

pages of Formal/Informal Drawings

Rule 312 Amendment/Letter

Small Entity

Large Entity

Req. for Acknowledgement of Cited Art

Declaration/Power of Attorney

Issue Fee

Recordation of Assignment/Security Agreement

Publication Fee

Information Disclosure Statement

Req. for Certificate of Correction

Form PTO 1449

Maintenance Fee for _____ years after grant

copies of cited references

Fee Address Indication Form

Preliminary Amendment

Terminal Disclaimer

Response to Missing Parts Notice

Petition to Commissioner

Resp. to Notice to Correct App. Papers

Status Inquiry

Certified Copy of Priority Doc.

Other Form 1050

Claim for Convention Priority

Response/Amendment to Office Action of

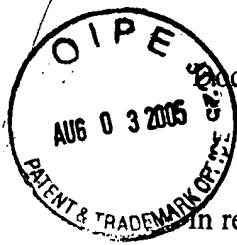
Request for _____ month Extension of Time

Check for \$	<input type="checkbox"/> Charge Deposit Acct. 500417	\$	Atty Init.	MEF	Tkpr. #	3328	Secy. or PL:	BDeHart
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CMS Descrip.: _____

THE PATENT AND TRADEMARK OFFICE DATE STAMPED HEREON IS ACKNOWLEDGEMENT THAT THE ITEMS, CHECKED ABOVE, WERE RECEIVED BY THE PTO ON THE DATE STAMPED





ocket No.: 061352-0041

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Hiroyuki FURUYA, et al.

Application No.: 10/620,432
Patent No. 6,806,109 B2

Filed: July 17, 2003

Issued: October 19, 2004

: Customer Number: 20277

: Confirmation Number: 2093

: Group Art Unit: 2812

: Examiner: MULPURI, SAVITRI

For: METHOD OF FABRICATING NITRIDE BASED SEMICONDUCTOR SUBSTRATE
AND METHOD OF FABRICATING NITRIDE BASED SEMICONDUCTOR DEVICE

REQUEST FOR CERTIFICATE OF CORRECTION UNDER 37 CFR 1.322

Mail Stop Box 4/ Certificates of Correction
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In reviewing the above-identified patent, a printing error was discovered therein requiring correction in order to conform the Official Record in the application.

The error noted is set forth on the attached copy of form PTO-1050 Rev. 2-93 in the manner required by the Commissioner's Notice.

Specifically, on the title page, side 1, Item "(56)", under "FOREIGN PATENT DOCUMENTS", the Korean reference --KR 2010583 A -- should be inserted. In addition, on side 2 of the title page, at the bottom of the listed "U.S. PATENT DOCUMENTS", the following U.S. Published application data should be inserted -- 2003/0203629 10/2005 Ishibashi et al438/689 --. Copies of the initialed PTO-1449 form listing the Korean application and PTO-892 listing the published application are attached for your information and convenience.

AUG 09 2005

The change requested herein occurred as a result of printing the Letters Patent and the Certificate should be issued without expense under Rule 322 of the Rules of Practice. Accordingly, Applicants request issuance of the Certificate of Correction.

Please charge any shortage in fees due in connection with the filing of this paper to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

McDERMOTT WILL & EMERY LLP

Michael E. Fogarty
Registration No. 36,139

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as our correspondence address.

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Date: May 26, 2005

WDC99 1087520-1.061352.0041

AUG 09 2005

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,806,109 B2

DATED : October 19, 2004

INVENTOR(S) : Hiroyuki FURUYA, et al.

It is certified that error appears in the above-identified patent and that said Letter Patent is hereby corrected as shown below:

ON THE TITLE PAGE, side 1,

Item ("56"), under "FOREIGN PATENT DOCUMENTS", insert the following:
-- KR 2010583 A -- ;

ON THE TITLE PAGE, side 2,

Below the listed "U.S. PATENT DOCUMENTS", insert

-- 2003/0203629 10/2005 Ishibashi et al438/689 -- .

1 AUG 09 2005